

Clean version of amended claims:

32. (Amended) An horological device comprising:

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a semiconductor substrate;
a first source region;
a first drain region;
a first channel region between the first source region
and the first drain region;
a first control gate;
a second source region;
a second drain region;
a second channel region between the second source region
and the second drain region;
a second control gate;
a floating gate, wherein a first portion of the floating
gate is between the first control gate and the first channel
region and a second portion of the floating gate is between
the second control gate and the second channel region; and
an insulating region comprising insulating material
substantially surrounding the floating gate, wherein the
insulating region comprises a tunneling region for discharging
an electrostatic charge stored in the floating gate through a
discharge process, wherein the tunneling region has one or
more physical properties that affect a rate of discharge in
the discharge process, and wherein at least one physical
property of the tunneling region has been selected so that the
discharge process discharges a stored electrostatic charge at
a predetermined rate.

41. (Amended) An article of manufacture comprising:
an analog time cell; and
a conductive lead for allowing a state of the analog time
cell to be modified or read.

Marked-up version of the amended claims--additions are shown with double-underlines and deletions are shown with strike-throughs.

32. (Amended) An horological device comprising:

- a semiconductor substrate;
- a first source region;
- a first drain region;
- a first channel region between the first source region and the first drain region;
- a first control gate;
- a second source region;
- a second drain region;
- a second channel region between the second source region and the second drain region;
- a second control gate;
- a floating gate, wherein a first portion of the floating gate is between the first control gate and the first channel region and a second portion of the floating gate is between the second control gate and the second channel region; and
- an insulating region comprising insulating material substantially surrounding the floating gate, wherein the insulating region comprises a tunneling region for discharging an electrostatic charge stored in the floating gate through a discharge process, wherein the tunneling region has one or more physical properties that affect a rate of discharge in the discharge process, and wherein at least one physical property of the tunneling region has been selected so that the